UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/549,279	10/19/2005	Tomohiko Takeda	125328	2470
²⁵⁹⁴⁴ OLIFF & BERI	7590 05/14/200 RIDGE, PLC	7	EXAMINER	
P.O. BOX 1992 ALEXANDRIA	2.8	CHEN, KEATH T		
ALEXANDRIA	1, VA 2232U		ART UNIT	PAPER NUMBER
			1709	
			MAN DATE	DEL MEDA MODE
			MAIL DATE	DELIVERY MODE
			05/14/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

				- 10		
		Application No.	Applicant(s)			
		10/549,279	TAKEDA ET AL.			
	Office Action Summary	Examiner	Art Unit			
		Keath T. Chen	1709			
Period fo	The MAILING DATE of this communication apported by the second section apported by the second section apport	pears on the cover sheet	with the correspondence address			
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. D period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailined patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUN 136(a). In no event, however, may will apply and will expire SIX (6) MO e, cause the application to become	IICATION. a reply be timely filed DNTHS from the mailing date of this communication. ABANDONED (35 U.S.C. § 133).			
Status						
1)⊠	Responsive to communication(s) filed on <u>02 D</u>	<u> ecember 2005</u> .	·			
2a)□	<u> </u>					
3)	Since this application is in condition for allowa	nce except for formal ma	tters, prosecution as to the merits is			
	closed in accordance with the practice under to	Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.			
Dispositi	ion of Claims			٠		
4)🖂	Claim(s) 1 and 2 is/are pending in the applicat	ion.				
-	4a) Of the above claim(s) is/are withdra	•				
5)[Claim(s) is/are allowed.					
6)⊠	Claim(s) 1 and 2 is/are rejected.	•	•			
· 7)	Claim(s) is/are objected to.	+				
8)[Claim(s) are subject to restriction and/o	or election requirement.	·			
Applicati	on Papers					
9)	The specification is objected to by the Examine	er.				
	The drawing(s) filed on is/are: a) ☐ acc	'	by the Examiner.			
	Applicant may not request that any objection to the	drawing(s) be held in abeya	ance. See 37 CFR 1.85(a).			
	Replacement drawing sheet(s) including the correct	tion is required if the drawin	g(s) is objected to. See 37 CFR 1.121(d).			
11)	The oath or declaration is objected to by the Ex	caminer. Note the attache	ed Office Action or form PTO-152.			
Priority u	ınder 35 U.S.C. § 119					
	Acknowledgment is made of a claim for foreign ☑ All b) ☐ Some * c) ☐ None of:	priority under 35 U.S.C.	§ 119(a)-(d) or (f).			
۵٫۱	1. Certified copies of the priority document	s have been received				
	2. Certified copies of the priority document		Application No			
	3. Copies of the certified copies of the prio		• •			
	application from the International Bureau	_ ·				
* S	See the attached detailed Office action for a list	• • • • • • • • • • • • • • • • • • • •	t received.			
			•			
			·	;		
Attachmen				٠		
	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948)		Summary (PTO-413) (s)/Mail Date	-		
3) 🛛 Inform	nation Disclosure Statement(s) (PTO/SB/08) r No(s)/Mail Date 01/05/2006, 10/19/2005.		Informal Patent Application			

Application/Control Number: 10/549,279

Art Unit: 1709

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

1. Claims 1-2 are rejected under 35 U.S.C. 102(b) as being anticipated by Tomioka (US 5810963, hereafter, '963).

'963' teaches all the limitation of claim 1:

A substrate processing apparatus (Fig. 1, #1, see also '963, claim 1), which has a high frequency power supply part (#5) with a controllable high frequency power source (#10 controller controls #9 matching unit and #15 gate), applies a high frequency power from the high frequency power source to a discharge electrode (#3) provided in a processing chamber (#1) through a matching unit (#9), and generates a plasma in the processing chamber (col. 6, lines 26-28), comprising:

at least a detector (#11) provided between the high frequency power source (#5) and the matching unit (#9) (the reflected wave from electrode #3 pass through matching unit #9, dircoup #8, path #8b, to detector #11, #13,-16, arrives at #6. Therefore, #11 detector is between matching unit #6 and RF power source #5), or between the matching unit and the discharge electrode, for detecting a reflected wave of the high frequency power reflected from the discharge electrode (col. 3, lines 42-44); and

a controller (#10) controlling the high frequency power source (through switch #6) so as to temporarily stop (col. 7, lines 48-52) or temporarily decrease (col. 11, lines 8-11, also see '963, claim 3) an application of the high frequency power to the discharge electrode, in accordance with a detection result of the detector (col. 7, lines 39-52 and col. 7, lines 26-34),

wherein the controller (#10) functions to control the high frequency power source (though gate #15 and switch #6) so as to temporarily stop or temporarily decrease the application of the high frequency power to the discharge electrode, and when the high frequency power is applied again, continuously apply the high frequency power without temporarily stopping (col. 7, line 60 to col. 8 line 3) or temporarily decreasing (col. 11, lines 8-11) the application of the high frequency power before a predetermined time period passes (col. 8, lines 17-19, see also '963 claim 6), and after the predetermined time period passes, temporarily stop or temporarily decrease the application of the high frequency power to the discharge electrode in accordance with the detection result of the detector (col. 8, lines 4-16).

'963 teaches all the limitation of claim 2:

A substrate processing method (see '963, claim 13) for processing a substrate by inserting a substrate in a processing chamber, exhausting an atmosphere out of the processing chamber while introducing the gas thereinto (col. 5, lines 63-67), applying the high frequency power to the discharge electrode from the high frequency power source through a matching unit (col. 5, last line to col. 6, line 6), and thereby generating

Application/Control Number: 10/549,279

Art Unit: 1709

a plasma in the processing chamber (col. 6, lines 7-10), wherein an application of the high frequency power is controlled to make it possible to:

temporarily stop (col. 7, line 60 to col. 8, line 3, see also '963, claim 17) or temporarily decrease (col. 11, lines 8-11, also see '963, claim 15) the application of a high frequency power to a discharge electrode when a reflected wave of the high frequency power from the discharge electrode is detected (col. 3, lines 42-44 and col. 7, lines 26-34); thereafter when the high frequency power is applied again,

continuously apply the high frequency power without temporarily stopping or temporarily decreasing the application of the high frequency power before a predetermined time period passes (see '963, claim 18); and after a predetermined time period passes,

temporarily stop or temporarily decrease the application of the high frequency power to the discharge electrode when the reflected wave is detected (col. 8, lines 4-16).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Keath T. Chen whose telephone number is 571-270-1870. The examiner can normally be reached on M-F, 8:30-5:00 EST.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Cleveland can be reached on 571-272-1418. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 1709

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

kc

JENNA BEFUMO